N-Channel 30-V (D-S) MOSFET With Schottky Diode

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low r _{DS(on)} provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY						
$V_{DS}(V)$ $r_{DS(on)} m(\Omega)$ $I_{D}(A)$						
30	$63 @ V_{GS} = 4.5V$	3.5				
30	$110 @ V_{GS} = 2.5V$	3.0				

SCHOTTKY PRODUCT SUMMARY						
V _{KA} (V)	$V_{KA}(V)$ $V_f(V)$ Diode Forward Voltage					
30	0.48V @ 1.0A	1.0				

	TSOP	-6				
	Top Vi	ew			D	K
]		L.	٩
ΑП	1	6	□K	_	岀	1
s 🗆	2	5	□ N/C	G	<u></u>	Ţ
GΠ	3	4	⊞Þ	N-Channe	S el MOSFET	Α

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Limit	Units					
Drain-Source Voltage (MOSFET)		$V_{ m DS}$	30					
Reverse Voltage (Schottky)		V_{KA}	30	V				
Gate-Source Voltage (MOSFET)		V_{GS}	±12					
Continuous Drain Current (T _J =150°C) (MOSFET) ^a	Continuous Drain Current (T=150°C) (MOSEET) ^a $T_A=25^{\circ}C$							
Continuous Diani Cuitchi (1)—130 C) (MOSI E1)	T _A =70°C	I_{D}	± 2.8	A				
Pulsed Drain Current (MOSFET) ^b		I_{DM}	± 16					
Continuous Source Current (MOSFET Diode Conduction) ^a		I_S	1.25					
Average Forward Current (Schottky)		I_{F}	0.5					
Pulsed Forward Current (Schottky)		I_{FM}	8					
Maximum Power Dissipation (MOSFET) ^a	$T_A=25^{\circ}C$	P_{D}	1.3					
Maximum Fower Dissipation (MOSFET)	$T_A=70^{\circ}C$	ТБ	0.8	W				
$T_A=25^{\circ}C$			1.0	, vv				
Maximum Power Dissipation (Schottky) ^a	$T_A=70^{\circ}C$		0.6					
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C				

THERMAL RESISTANCE RATINGS								
Parameter		Symbol	Maximum	Units				
	t <= 10 sec	D	100	°C/W				
Maximum Junction-to-Ambient ^a	Steady-State	$R_{ heta JA}$	166	°C/W				

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM3836N

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)								
Downwoton	Cymrh ol	T		Limits				
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	0.7			V		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = 12 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current	I	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA		
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	6			Α		
D : G . C . D : . A		$V_{GS} = 4.5 \text{ V}, I_D = 3.5 \text{ A}$ $V_{GS} = 2.5 \text{ V}, I_D = 3 \text{ A}$			63	mΩ		
Drain-Source On-Resistance ^A	r _{DS(on)}				110			
Forward Tranconductance ^A	\mathbf{g}_{fs}	$V_{DS} = 15 \text{ V}, I_D = 3.5 \text{ A}$		6.9		S		
Diode Forward Voltage	V_{SD}	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.8		V		
Dynamic ^b								
Total Gate Charge	Qg	V = 15 V V = 45 V		6.3				
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 3.5 \text{ A}$		0.9		пC		
Gate-Drain Charge	Q_{gd}	I _D – 3.3 A		1.9				
Turn-On Delay Time	t _{d(on)}			16				
Rise Time	$t_{\rm r}$	$V_{DD} = 25 \text{ V}, R_L = 25 \Omega, I_D = 1 \text{ A},$		5		C		
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}$		23		nS		
Fall-Time	t_{f}			3				

SCHOTTKY SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)								
Parameter	Cumahaal	Tast Canaditions	Limits			I Imit		
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Forward Voltage Drop	V _F	$I_F = 0.5 A$			0.48	V		
Forward Voltage Drop		$I_F = 0.5 \text{ A}, T_J = 125^{\circ}\text{C}$			0.4	V		
		$V_{r} = 30 \text{ V}$			0.1			
Maximum Reverse Leakage Current	I_{rm}	$V_r = 30 \text{ V}, T_J = 75^{\circ}\text{C}$			1	mΑ		
		$V_r = 30 \text{ V}, T_J = 125^{\circ}\text{C}$			10			
Junction Capacitance	C _T	$V_r = 10 \text{ V}$		31		pF		

Notes

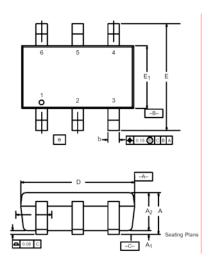
- a. Pulse test: $PW \le 300us duty cycle \le 2\%$.
- b. Guaranteed by design, not subject to production testing.

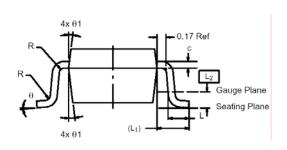
Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.

Analog Power AM3836N

Package Information

TSOP-6: 6LEAD





	MIL	LIMET	ERS	ı	NCHES	;
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	_	0.043
Α1	0.01	-	0.10	0.0004	-	0.004
A ₂	0.84	_	1.00	0.033	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
Е	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
е		1.00 BSC		(0.0394 BSC	;
L	0.35	-	0.50	0.014	_	0.020
L ₁		0.60 Ref			0.024 Ref	
L ₂		0.25 BSC			0.010 BSC	
R	0.10	_	_	0.004	_	_
θ	0°	4°	8°	0°	4°	8°
θ_1		7° Nom			7° Nom	